

isc Silicon NPN Power Transistor

KSD5059

DESCRIPTION

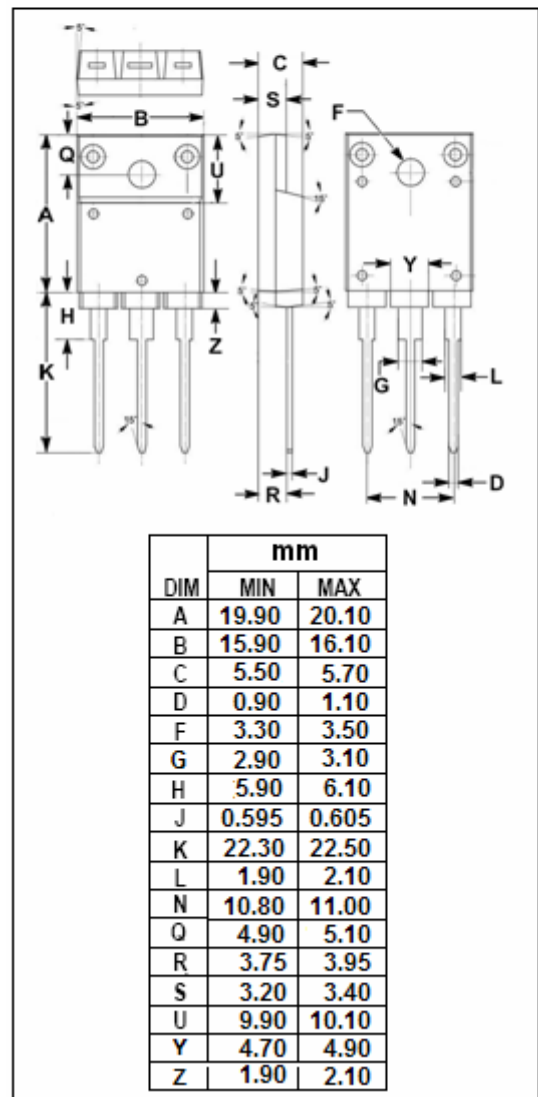
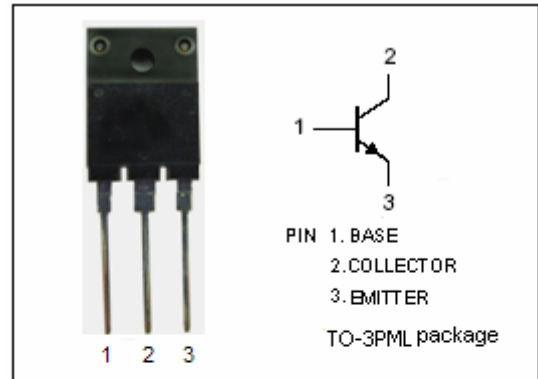
- High Breakdown Voltage-  
:  $V_{CBO} = 1500V$  (Min)
- High Switching Speed
- High Reliability

APPLICATIONS

- Designed for color monitor horizontal output applications

ABSOLUTE MAXIMUM RATINGS( $T_a=25^\circ C$ )

SYMBOL	PARAMETER	VALUE	UNIT
$V_{CBO}$	Collector-Base Voltage	1500	V
$V_{CEO}$	Collector-Emitter Voltage	800	V
$V_{EBO}$	Emitter-Base Voltage	6	V
$I_C$	Collector Current- Continuous	6	A
$I_{CP}$	Collector Current-Peak	20	A
$P_C$	Collector Power Dissipation @ $T_C=25^\circ C$	60	W
$T_J$	Junction Temperature	150	$^\circ C$
$T_{stg}$	Storage Temperature Range	-55~150	$^\circ C$



**isc Silicon NPN Power Transistor****KSD5059****ELECTRICAL CHARACTERISTICS****T<sub>C</sub>=25°C unless otherwise specified**

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V <sub>CEO(SUS)</sub>	Collector-Emitter Sustaining Voltage	I <sub>C</sub> = 100mA; I <sub>B</sub> = 0	800			V
V <sub>CE(sat)</sub>	Collector-Emitter Saturation Voltage	I <sub>C</sub> = 5A; I <sub>B</sub> = 1A			5.0	V
V <sub>BE(sat)</sub>	Base-Emitter Saturation Voltage	I <sub>C</sub> = 5A; I <sub>B</sub> = 1A			1.5	V
I <sub>CBO</sub>	Collector Cutoff Current	V <sub>CB</sub> = 800V ; I <sub>E</sub> = 0			10	μ A
I <sub>CES</sub>	Collector Cutoff Current	V <sub>CE</sub> = 1500V ; V <sub>BE</sub> = 0			1	mA
I <sub>EBO</sub>	Emitter Cutoff Current	V <sub>EB</sub> = 4V ; I <sub>C</sub> = 0			1	mA
h <sub>FE-1</sub>	DC Current Gain	I <sub>C</sub> = 1A ; V <sub>CE</sub> = 5V	8			
h <sub>FE-2</sub>	DC Current Gain	I <sub>C</sub> = 5A ; V <sub>CE</sub> = 5V	3			
t <sub>f</sub>	Fall Time	I <sub>C</sub> = 4A , I <sub>B1</sub> = 0.8A ; I <sub>B2</sub> = -1.6A			0.3	μ s